

Abdelhakim Latreche

List of Publications by Year in descending order

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15
papers

106
citations

1478505

6
h-index

1372567

10
g-index

15
all docs

15
docs citations

15
times ranked

104
citing authors

#	ARTICLE	IF	CITATIONS
1	Modified expressions of field and thermionic-field emission for Schottky barrier diodes in the reverse regime. <i>Semiconductor Physics, Quantum Electronics and Optoelectronics</i> , 2021, 24, 16-21.	1.0	2
2	Determination of temperature dependence of electron effective mass in 4H-SiC from reverse current-voltage characteristics of 4H-SiC Schottky barrier diodes. <i>Semiconductor Physics, Quantum Electronics and Optoelectronics</i> , 2020, 23, 271-275.	1.0	1
3	Combined thermionic emission and tunneling mechanisms for the analysis of the leakage current for Ga ₂ O ₃ Schottky barrier diodes. <i>SN Applied Sciences</i> , 2019, 1, 1.	2.9	13
4	Validity of the Padovani-Stratton formulas for analysis of reverse current-voltage characteristics of 4H-SiC Schottky barrier diodes. <i>Semiconductor Science and Technology</i> , 2019, 34, 055021.	2.0	5
5	Conduction mechanisms of the reverse leakage current of 4H-SiC Schottky barrier diodes. <i>Semiconductor Science and Technology</i> , 2019, 34, 025016.	2.0	10
6	Combination of thermionic emission and tunneling mechanisms to analyze the leakage current in 4H-SiC Schottky barrier diodes. <i>Semiconductor Physics, Quantum Electronics and Optoelectronics</i> , 2019, 22, 19-25.	1.0	7
7	Conduction mechanisms of the reverse leakage current of β -Ga ₂ O ₃ Schottky barrier diodes. <i>Semiconductor Physics, Quantum Electronics and Optoelectronics</i> , 2019, 22, 397-403.	1.0	5
8	Comment on "Pressure Induced Phase Transition, Elastic and Thermal Properties of Rare Earth Tellurides". <i>Transactions of the Indian Institute of Metals</i> , 2017, 70, 1159-1160.	1.5	1
9	Comment on "Density functional investigation on electronic structure and elastic properties of BeX at high pressure". <i>Indian Journal of Physics</i> , 2016, 90, 1243-1244.	1.8	3
10	Temperature dependence of the inhomogeneous parameters of the Mo/4H-SiC Schottky barrier diodes. <i>Semiconductor Science and Technology</i> , 2016, 31, 085008.	2.0	12
11	Comment on "Debye temperature and melting point of II-VI and III-V semiconductors". [<i>Cryst. Res. Technol.</i> 45, No. 9, 920-924 (2010)]. <i>Crystal Research and Technology</i> , 2016, 51, 115-116.	1.3	3
12	New study of the abnormal behavior of the low temperature dependence of the current in inhomogeneous Schottky diode. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , 2015, 28, 231-238.	1.9	2
13	Reverse bias-dependence of schottky barrier height on silicon carbide: influence of the temperature and donor concentration. <i>International Journal of Physical Research</i> , 2014, 2, .	0.5	7
14	Modified Airy function method modelling of tunnelling current for Schottky barrier diodes on silicon carbide. <i>Semiconductor Science and Technology</i> , 2013, 28, 105003.	2.0	15
15	Electrical characteristics of Mo/4H-SiC Schottky diodes having ion-implanted guard rings: temperature and implant-dose dependence. <i>Semiconductor Science and Technology</i> , 2011, 26, 085003.	2.0	20